Product data sheet

1. General description

PNP low V_{CEsat} transistor in a medium power SOT223 (SC-73) Surface-Mounted Device (SMD) plastic package.

2. Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability: I_C and I_{CM}
- · Higher efficiency leading to less heat generation
- Qualified according to AEC-Q101 and recommended for use in automotive applications

3. Applications

- DC-to-DC conversion
- · Supply line switching
- · Battery charger
- LCD backlighting
- Driver in low supply voltage applications (e.g. lamps and LEDs)
- Inductive load driver (e.g. relays, buzzers and motors)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	-40	V
Ic	collector current		-	-	-2	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	-3	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = -1 A; I_B = -100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	320	mΩ



40 V; 2 A PNP low VCEsat transistor

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	4	C
2	С	collector		В
3	E	emitter		P
4	С	collector	1 2 3	Ė
			SC-73 (SOT223)	sym028

6. Ordering information

Table 3. Ordering information

Type number	Package						
	Name	Description	Version				
PBSS5240Z-Q	SC-73	plastic, surface-mounted package with increased heatsink; 4 leads; 2.3 mm pitch; 6.5 mm x 3.5 mm x 1.65 mm body	<u>SOT223</u>				

7. Marking

Table 4. Marking codes

Type number	Marking code
PBSS5240Z-Q	S5240Z

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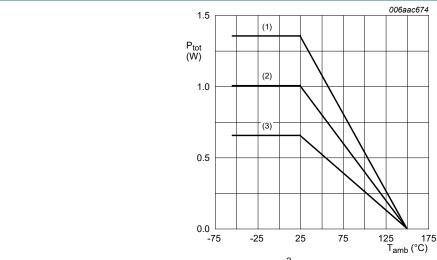
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	-40	V
V _{CEO}	collector-emitter voltage	open base		-	-40	V
V _{EBO}	emitter-base voltage	open collector		-	-7	V
I _C	collector current			-	-2	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-3	А
I _B	base current			-	-300	mA
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms		-	-1	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	0.65	W
			[2]	-	1	W
			[3]	-	1.35	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

- Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm². Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm². [3]



- (1) FR4 PCB, mounting pad for collector 6 cm²
- (2) FR4 PCB, mounting pad for collector 1 cm²
- (3) FR4 PCB, standard footprint

Power derating curves Fig. 1.

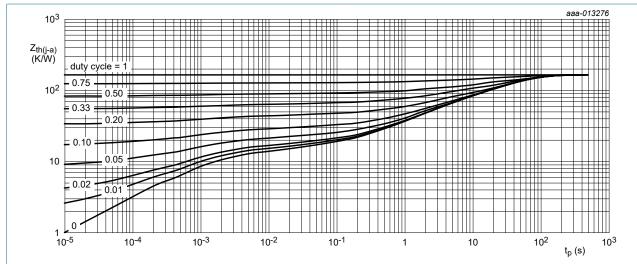
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9. Thermal characteristics

Table 6. Thermal characteristics

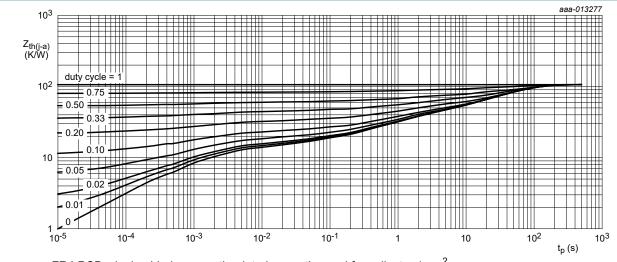
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from]	[1]	-	-	192	K/W
	junction to ambient		[2]	-	-	125	K/W
			[3]	-	-	93	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	16	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².



FR4 PCB, single-sided copper, tin-plated and standard footprint.

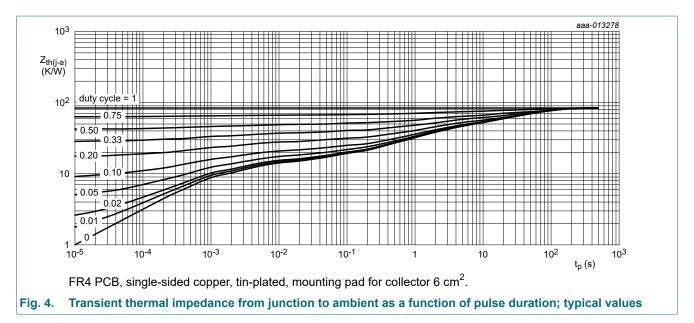
Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
І _{сво}	collector-base cut-off	V _{CB} = -32 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-100	nA
	current	V _{CB} = -32 V; I _E = 0 A; T _j = 150 °C	-	-	-50	μΑ
I _{CES}	collector-emitter cut-off current	V _{CE} = -32 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	-100	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
h _{FE}	DC current gain	V _{CE} = -5 V; I _C = -1 mA; T _{amb} = 25 °C	300	-	-	
		V_{CE} = -5 V; I_{C} = -500 mA; $t_{p} \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	215	-	-	
		V_{CE} = -5 V; I_{C} = -1 A; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	145	-	-	
		V_{CE} = -5 V; I_{C} = -2 A; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C; pulsed	55	-	-	
V _{CEsat}	collector-emitter saturation voltage	I _C = -100 mA; I _B = -1 mA; T _{amb} = 25 °C	-	-	-140	mV
		I_C = -500 A; I_B = -50 mA; $t_p \le 300 \mu s$; δ ≤ 0.02; T_{amb} = 25 °C	-	-	-170	mV
		I_C = -1 A; I_B = -100 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	-320	mV
		I_C = -2 A; I_B = -200 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	-650	mV
R _{CEsat}	collector-emitter saturation resistance	I_C = -1 A; I_B = -100 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	320	mΩ
V _{BEsat}	base-emitter saturation voltage		-	-	-1.2	V
V_{BEon}	base-emitter turn-on voltage	V_{CE} = -5 V; I_{C} = -1 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	-1.1	V
fт	transition frequency	V_{CE} = -10 V; I_{C} = -50 mA; f = 100 MHz; T_{amb} = 25 °C	150	-	-	MHz
C _c	collector capacitance	V _{CB} = -10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	-	12	pF

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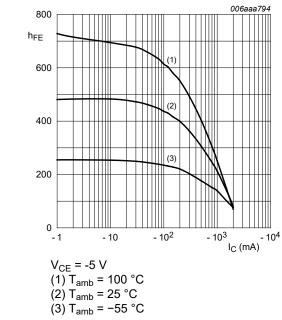


Fig. 5. DC current gain as a function of collector current; typical values

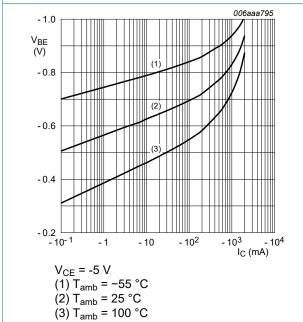


Fig. 7. Base-emitter voltage as a function of collector current; typical values

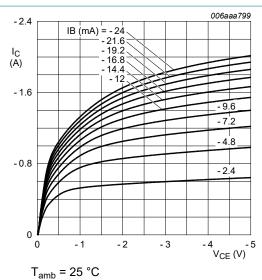
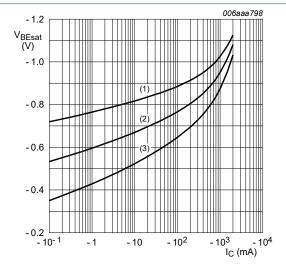


Fig. 6. Collector current as a function of collectoremitter voltage; typical values



 $I_{\rm C}/I_{\rm B}=20$

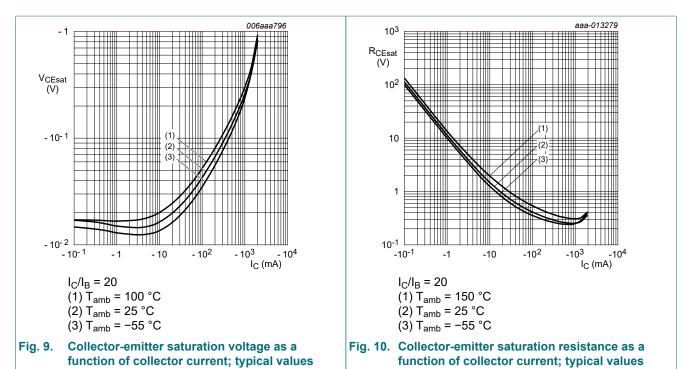
(1) T_{amb} = -55 °C

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = 150 \, ^{\circ}C$

Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values

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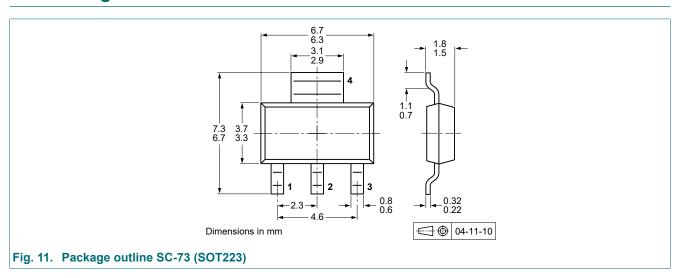


11. Test information

Quality information

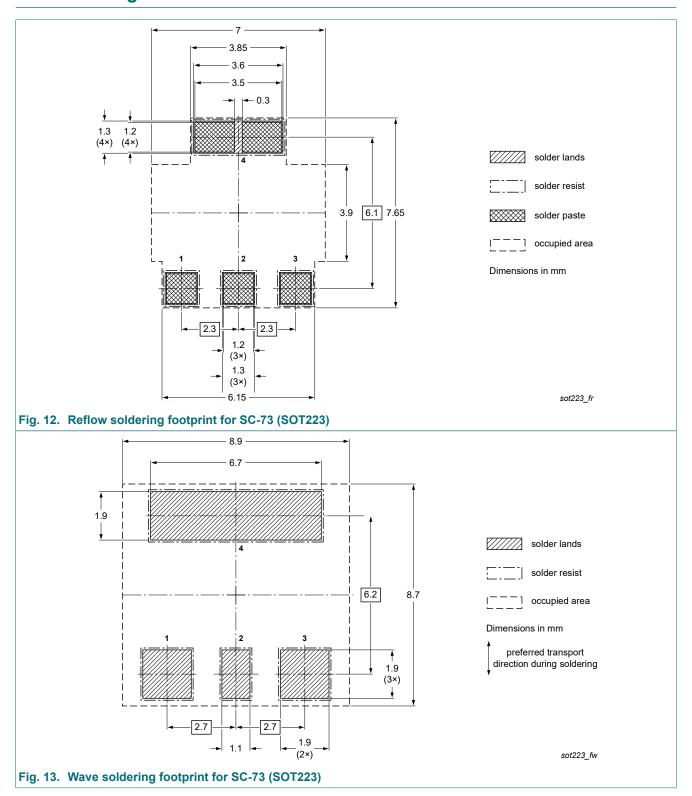
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS5240Z-Q v.1	20250326	Product data sheet	-	-

40 V; 2 A PNP low VCEsat transistor

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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